DRC3113Z

Silicon NPN epitaxial planar type

For digital circuits Complementary to DRA3113Z DRC9113Z in SSSMini3 type package

Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Packaging

Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

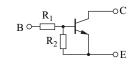
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	50	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Collector current	I _C	100	mA	
Total power dissipation	P _T	100	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Package

- Code
- SSSMini3-F2-B
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector

Marking Symbol: N1

Internal Connection



Resistance value	R ₁	1	kΩ
	R ₂	10	kΩ

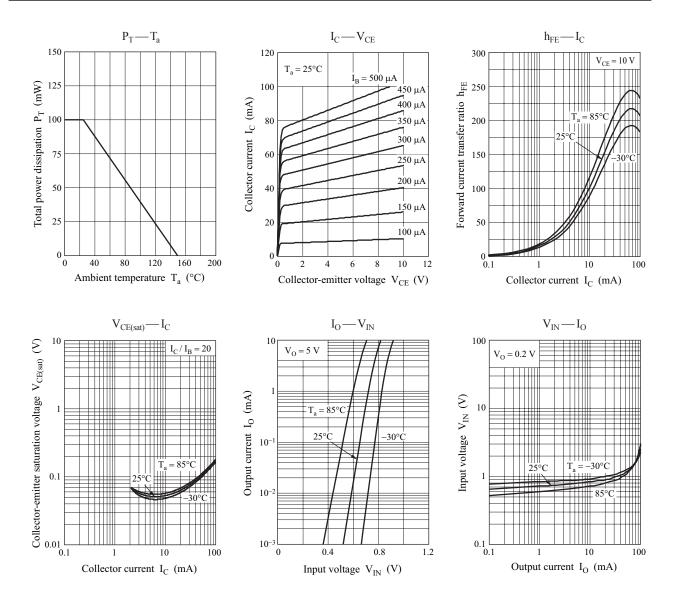
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6 V, I_C = 0$			1.5	mA
Forward current transfer ratio	\mathbf{h}_{FE}	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	30			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	V _{I(on)}	$V_{CE} = 0.2 \text{ V}, I_C = 5 \text{ mA}$	1.0			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = 5 \text{ V}, I_C = 100 \ \mu\text{A}$			0.4	V
Input resistance	R ₁		-30%	1	+30%	kΩ
Resistance ratio	R_1/R_2		0.08	0.10	0.12	

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

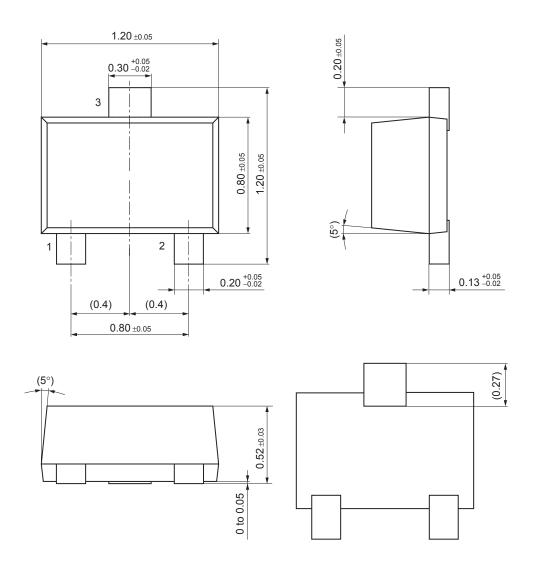
DRC3113Z

Panasonic



SSSMini3-F2-B

Unit: mm



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